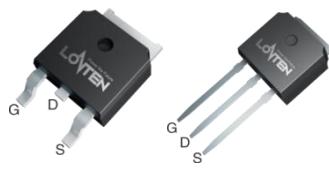
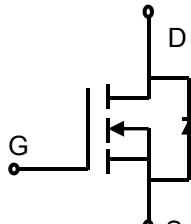


Lonten N-channel 40V, 39A, 16.5mΩ Power MOSFET

Description	Product Summary
<p>These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.</p>	<p>V_{DSS} 40V $R_{DS(on),max}@ V_{GS}=10V$ 16.5mΩ I_D 39A</p>
	Pin Configuration
	 <p>TO-252 TO-251</p>
<h3>Features</h3> <ul style="list-style-type: none"> ◆ 40V, 39A, $R_{DS(ON),max}=16.5m\Omega @ V_{GS}=10V$ ◆ Improved dv/dt capability ◆ Fast switching ◆ Green device available 	
<h3>Applications</h3> <ul style="list-style-type: none"> ◆ Motor Drives ◆ UPS ◆ DC-DC Converter 	<p>N-Channel MOSFET</p> 

Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Continuous drain current ($T_c = 25^\circ C$)	I_D	39	A
Continuous drain current ($T_c = 100^\circ C$)		24.5	A
Pulsed drain current ¹⁾	I_{DM}	156	A
Gate-Source voltage	V_{GSS}	± 20	V
Power Dissipation ($T_c = 25^\circ C$)	P_D	37	W
Avalanche energy ²⁾	E_{AS}	27.5	mJ
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.4	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking
LNG04R165	TO-252	LNG04R165
LNH04R165	TO-251	LNH04R165

Electrical Characteristics
 $T_J = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}}=0 \text{ V}, I_{\text{D}}=250 \mu\text{A}$	40	---	---	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250 \mu\text{A}$	1.0	1.5	2.0	V
Drain-source leakage current	I_{DSS}	$V_{\text{DS}}=40 \text{ V}, V_{\text{GS}}=0 \text{ V}, T_J = 25^\circ\text{C}$	---	---	1	μA
		$V_{\text{DS}}=32 \text{ V}, V_{\text{GS}}=0 \text{ V}, T_J = 125^\circ\text{C}$	---	---	10	μA
Gate leakage current, Forward	I_{GSSF}	$V_{\text{GS}}=20 \text{ V}, V_{\text{DS}}=0 \text{ V}$	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{\text{GS}}=-20 \text{ V}, V_{\text{DS}}=0 \text{ V}$	---	---	-100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=10 \text{ A}$	---	14.5	16.5	$\text{m}\Omega$
		$V_{\text{GS}}=4.5 \text{ V}, I_{\text{D}}=5 \text{ A}$	---	19.5	23	$\text{m}\Omega$
Forward transconductance	g_{fs}	$V_{\text{DS}}=5 \text{ V}, I_{\text{D}}=10 \text{ A}$	---	35	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{\text{DS}} = 20 \text{ V}, V_{\text{GS}} = 0 \text{ V}, F = 1 \text{ MHz}$	---	1061	---	pF
Output capacitance	C_{oss}		---	127	---	
Reverse transfer capacitance	C_{rss}		---	102	---	
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DD}} = 20 \text{ V}, V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 20 \text{ A}$	---	12.3	---	ns
Rise time	t_r		---	18.6	---	
Turn-off delay time	$t_{\text{d(off)}}$		---	47.2	---	
Fall time	t_f		---	16.3	---	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{\text{DS}}=20 \text{ V}, I_{\text{D}}=20 \text{ A}, V_{\text{GS}}=10 \text{ V}$	---	7.2	---	nC
Gate to drain charge	Q_{gd}		---	4.3	---	
Gate charge total	Q_g		---	24	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_s		---	---	39	A
Pulsed Source Current	I_{SM}		---	---	156	A
Diode Forward Voltage ²⁾	V_{SD}	$V_{\text{GS}}=0 \text{ V}, I_{\text{S}}=10 \text{ A}, T_J=25^\circ\text{C}$	---	---	1.2	V
Reverse Recovery Time	t_{rr}	$I_{\text{S}}=20 \text{ A}, dI/dt=100 \text{ A/us}, T_J=25^\circ\text{C}$	---	32	---	ns
Reverse Recovery Charge	Q_{rr}		---	24	---	nC

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

 2: $V_{\text{DD}}=20 \text{ V}, V_{\text{GS}}=10 \text{ V}, L=0.5 \text{ mH}, I_{\text{AS}}=10.5 \text{ A}, R_G=25 \Omega$, Starting $T_J=25^\circ\text{C}$.

 3: Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

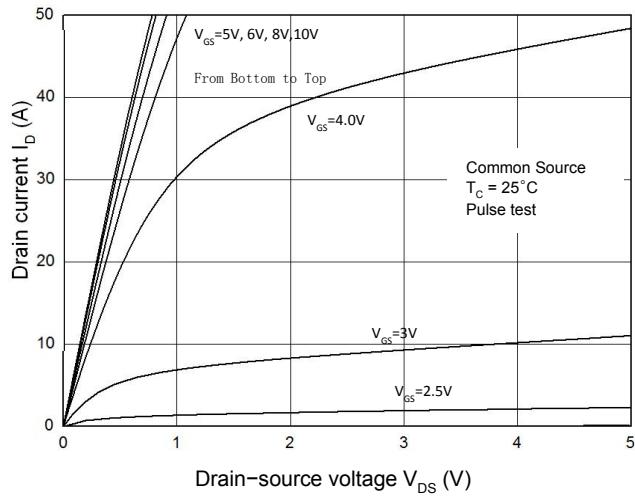


Figure 2. Transfer Characteristics

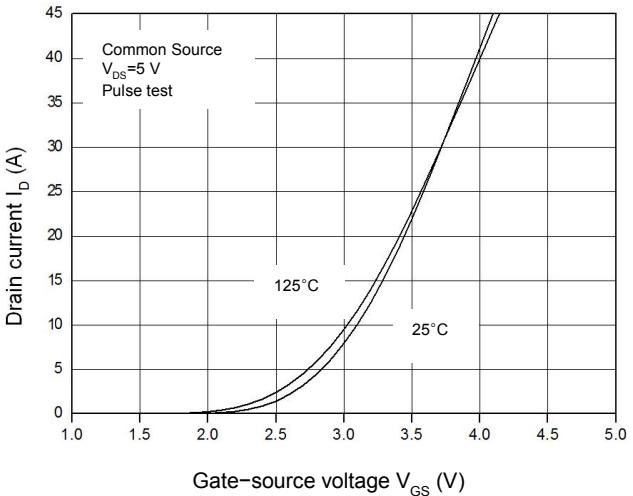


Figure 3. Capacitance Characteristics

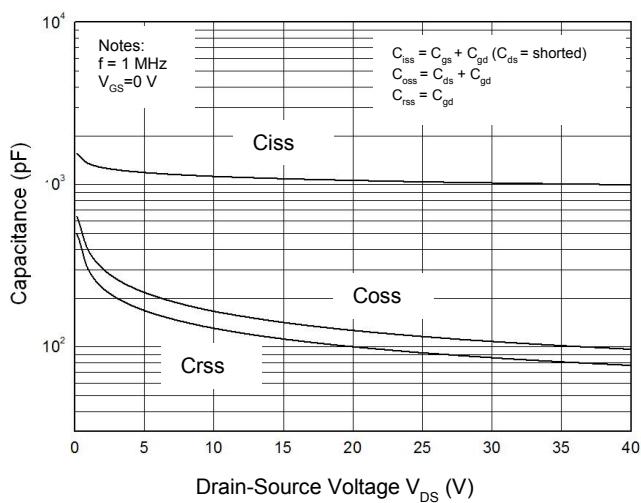


Figure 4. Gate Charge Waveform

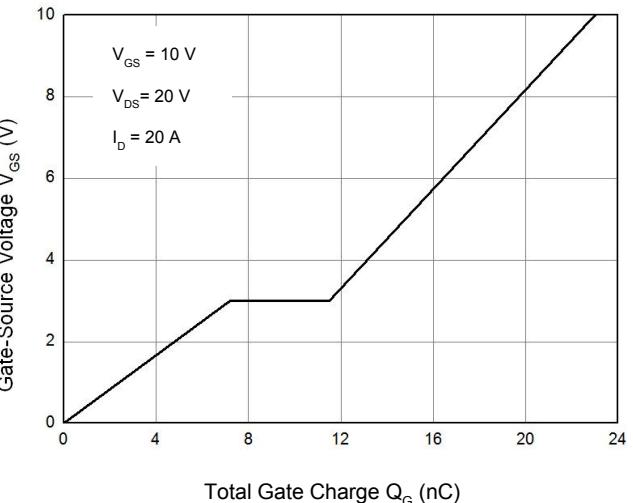


Figure 5. Body-Diode Characteristics

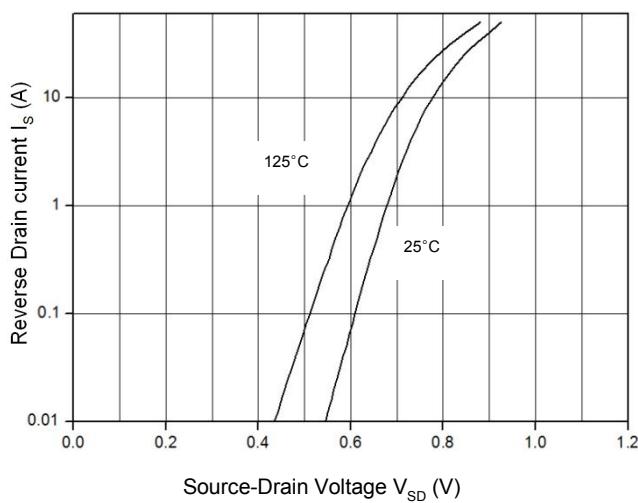


Figure 6. Rdson-Drain Current

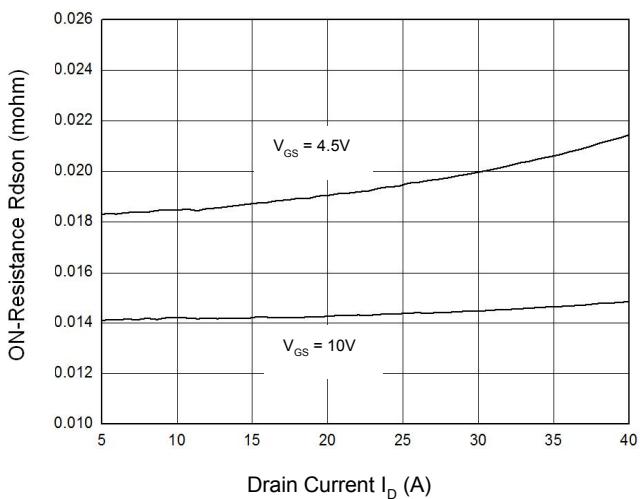


Figure 7. Rdson-Junction Temperature(°C)

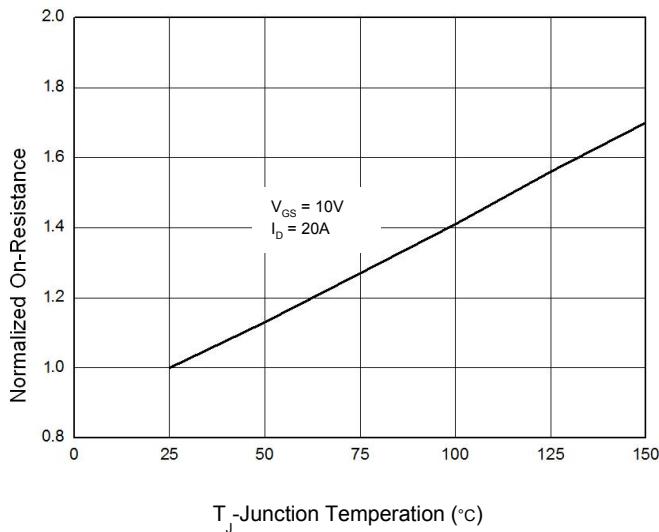


Figure 8. Maximum Safe Operating Area

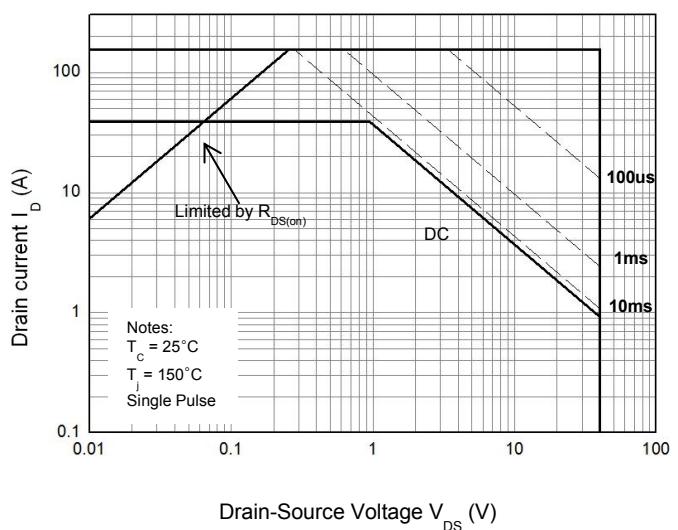
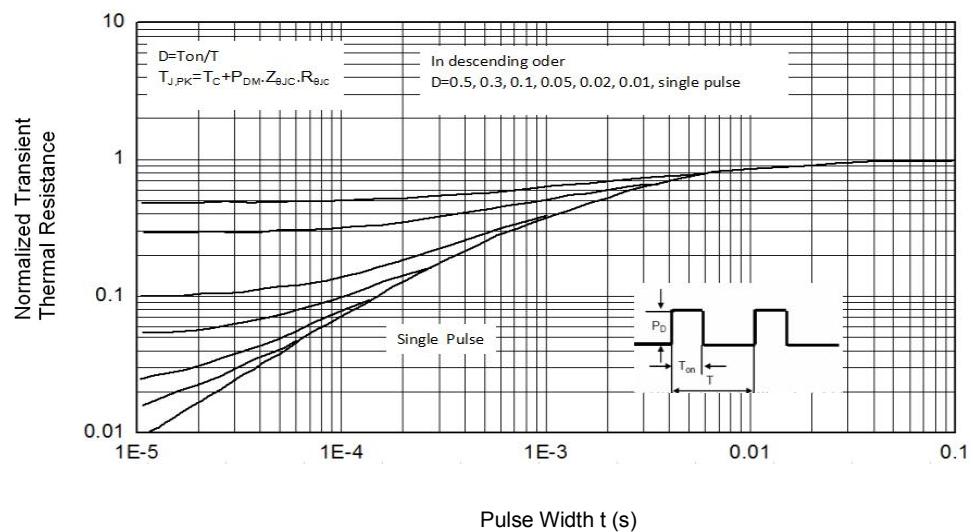


Figure 9. Normalized Maximum Transient Thermal Impedance (RthJA)



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

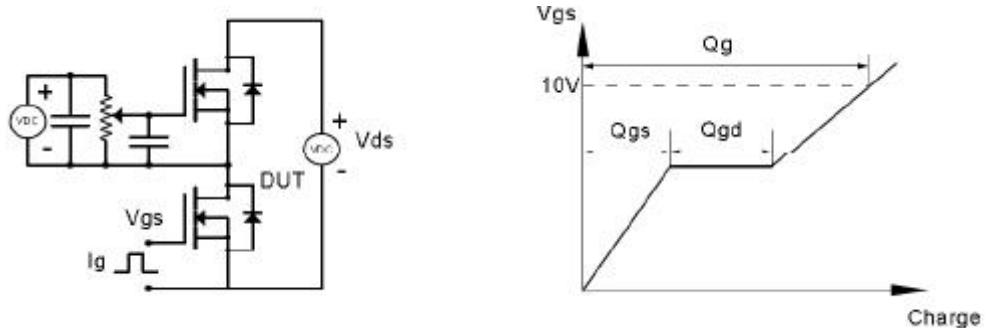


Figure 9. Resistive Switching Test Circuit & Waveforms

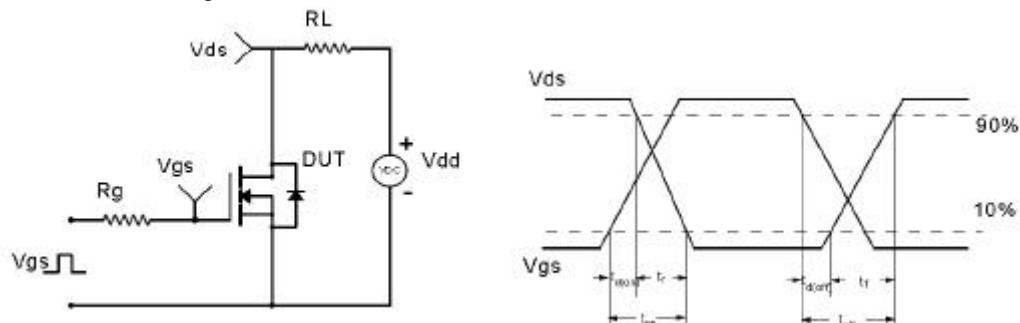


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

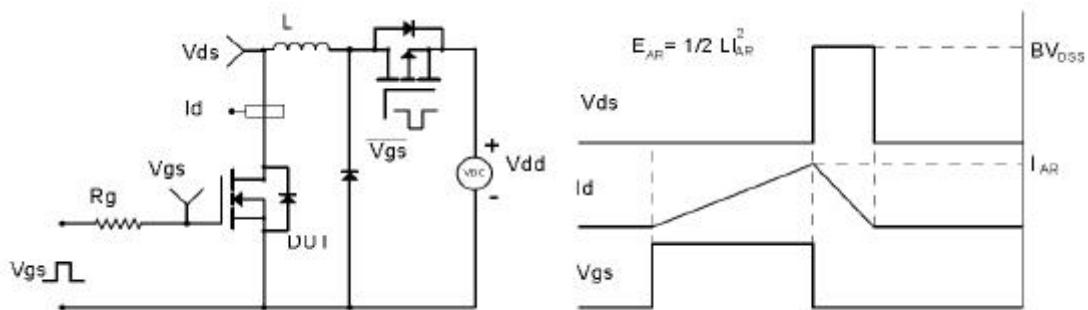
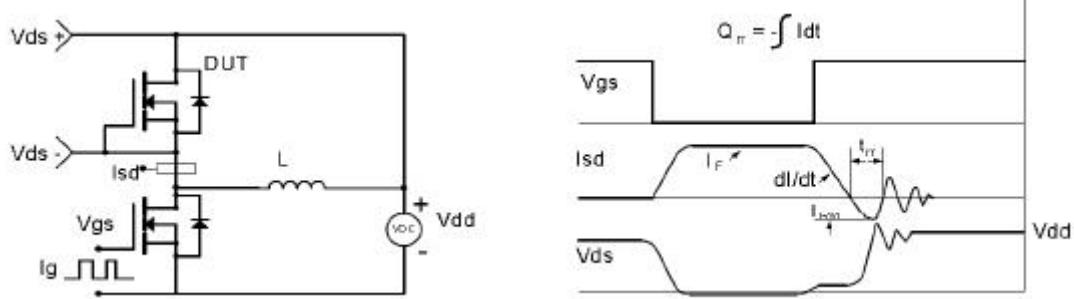
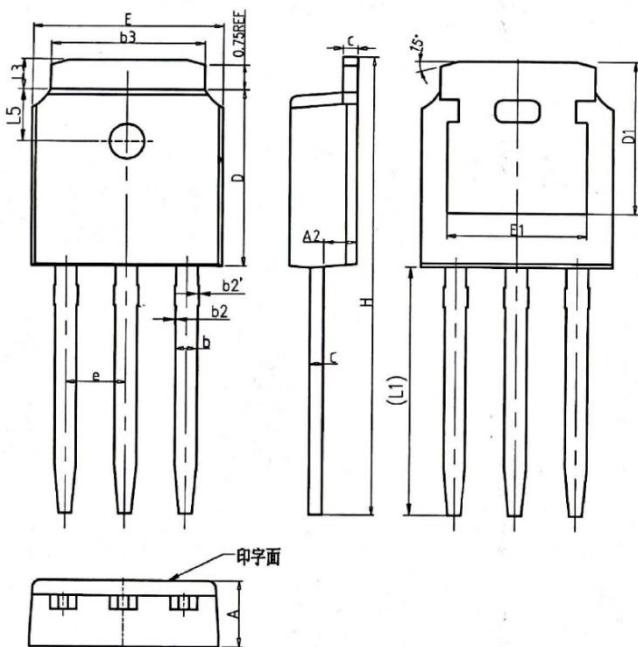


Figure 11. Diode Recovery Circuit & Waveform

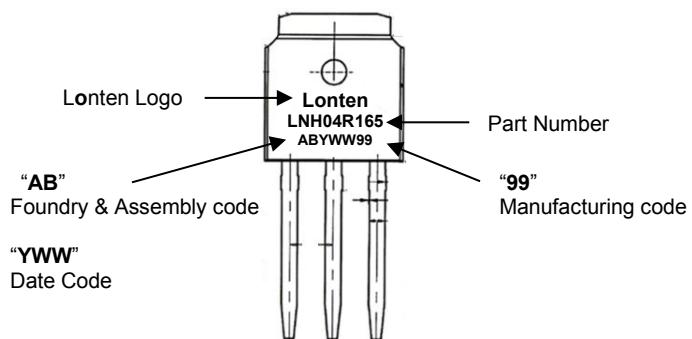


Mechanical Dimensions for TO-251

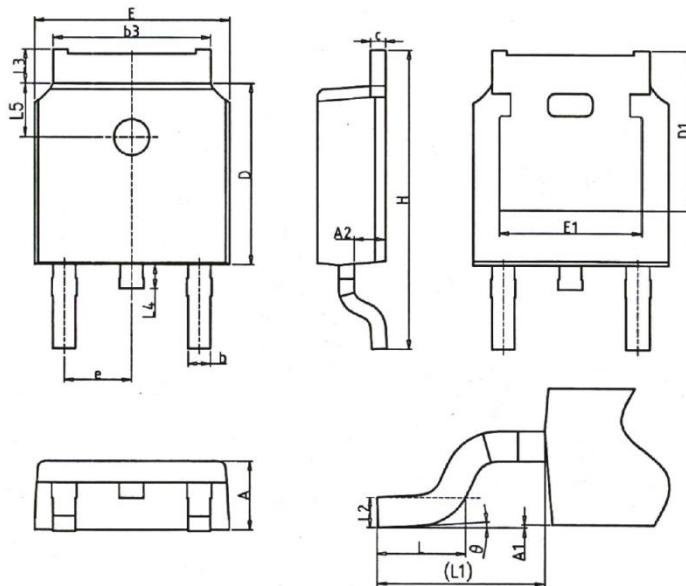


SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.20	2.30	2.38	0.087	0.091	0.094
A2	0.97	1.07	1.17	0.038	0.042	0.046
b	0.68	0.78	0.90	0.027	0.031	0.035
b2	0.00	0.04	0.10	0.000	0.002	0.004
b2'	0.00	0.04	0.10	0.000	0.002	0.004
b3	5.20	5.33	5.46	0.205	0.210	0.215
c	0.43	0.53	0.61	0.017	0.021	0.024
D	5.98	6.10	6.22	0.235	0.240	0.245
D1	5.30REF			0.209REF		
E	6.40	6.60	6.73	0.252	0.260	0.265
E1	4.63	-	-	0.182	-	-
e	2.286BSC			0.090BSC		
H	16.22	16.52	16.82	0.639	0.650	0.662
L1	9.15	9.40	9.65	0.360	0.370	0.380
L3	0.88	1.02	1.28	0.035	0.040	0.050
L5	1.65	1.80	1.95	0.065	0.071	0.077

TO-251 Part Marking Information

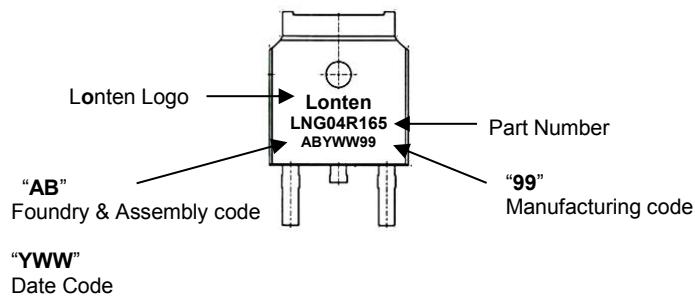


Mechanical Dimensions for TO-252



SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.20	2.30	2.38	0.087	0.091	0.094
A1	0.00	-	0.20	0.000	-	0.008
A2	0.97	1.07	1.17	0.038	0.042	0.046
b	0.68	0.78	0.90	0.027	0.031	0.035
b3	5.20	5.33	5.46	0.205	0.210	0.215
c	0.43	0.53	0.61	0.017	0.021	0.024
D	5.98	6.10	6.22	0.235	0.240	0.245
D1	5.30REF			0.209REF		
E	6.40	6.60	6.73	0.252	0.260	0.265
E1	4.63	-	-	0.182	-	-
e	2.286BSC			0.090BSC		
H	9.40	10.10	10.50	0.370	0.398	0.413
L	1.38	1.50	1.75	0.054	0.059	0.069
L1	2.90REF			0.114REF		
L2	0.51BSC			0.020BSC		
L3	0.88	-	1.28	0.035	-	0.050
L4	0.50	-	1.00	0.020	-	0.039
L5	1.65	1.80	1.95	0.065	0.071	0.077
θ	0°	-	8°	0°	-	8°

TO-252 Part Marking Information



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